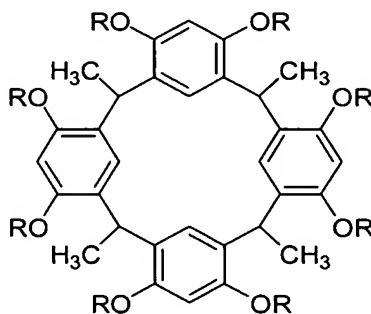


IN THE CLAIMS

Please amend the claims as follows:

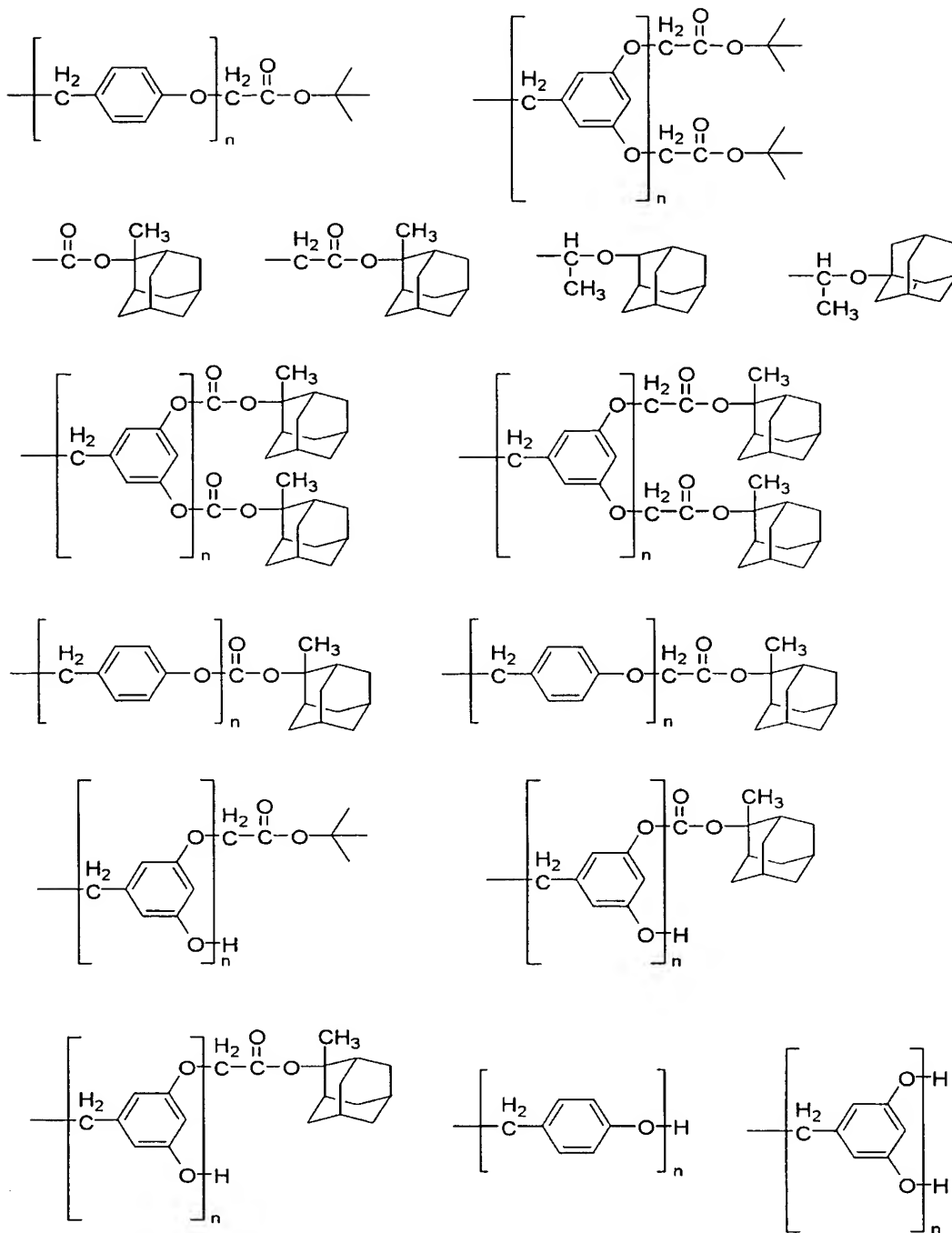
Claims 1-17 (Canceled).

Claim 18 (New): A calixresorcinarene compound shown by formula (1),



(1)

wherein R individually represents a hydrogen atom, a 1-tetrahydropyranyl group, a 1-tetrahydrofuranyl group, or one or more organic groups selected from the group consisting of the organic groups shown by the following formulas,



wherein n individually represents an integer of 1 to 50,

provided that a compound in which R is selected only from a hydrogen atom, a 1-tetrahydropyranyl group, and a 1-tetrahydrofuranyl group is excluded.

Claim 19 (New): A method for the purification of a calixresorcinarene compound according to claim 18 comprising washing said compound with an acidic aqueous solution and processing the washed compound with an ion-exchange resin.

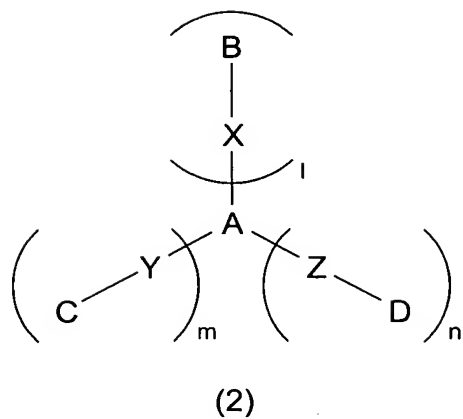
Claim 20 (New): A photoresist base material for extreme ultraviolet radiation and/or an electron beam comprising the calixresorcinarene compound according to claim 18 and shown by formula (1).

Claim 21 (New): A photoresist composition for extreme ultraviolet radiation and/or an electron beam comprising the photoresist base material according to claim 20 and a solvent.

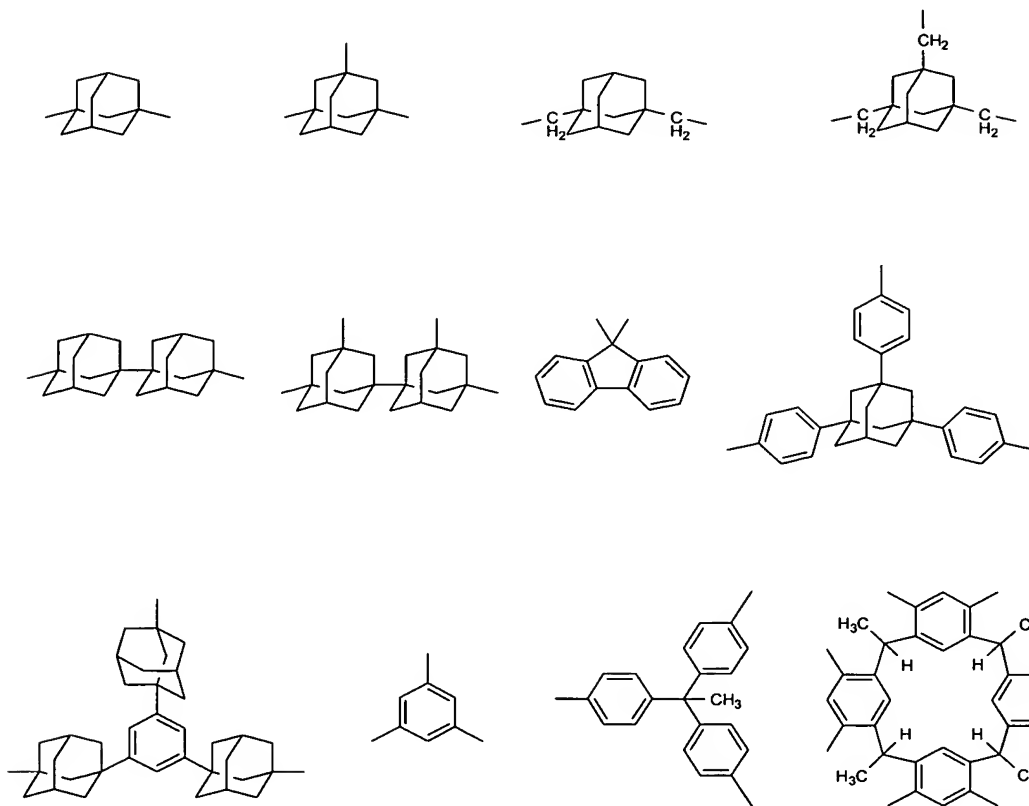
Claim 22 (New): The photoresist composition according to claim 21, further comprising a photoacid generator.

Claim 23 (New): The photoresist composition according to claim 21, further comprising a basic organic compound as a quenching agent.

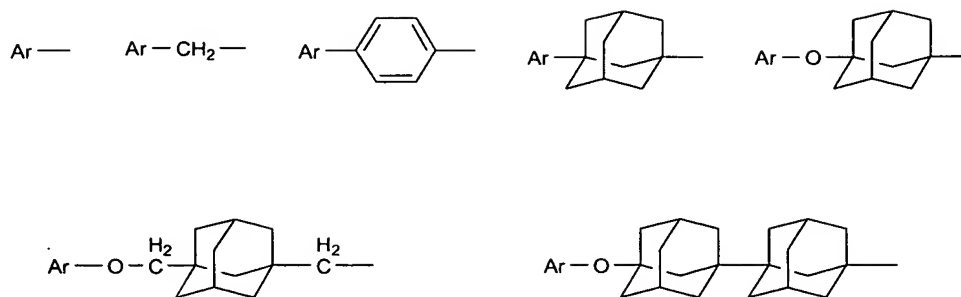
Claim 24 (New): A photoresist composition comprising a photoresist base material that is an extreme ultraviolet radiation-reactive organic compound shown by formula (2), obtained by washing with an acidic aqueous solution and processing with an ion-exchange resin, a photoacid generator or a photobase generator, and a quenching agent,



wherein A is an organic group represented by one of the following formulas,



B, C, and D are individually a group reactive with extreme ultraviolet radiation, a group reactive with an effect of a chromophore active to extreme ultraviolet radiation, or an organic group of any of the following formulas,

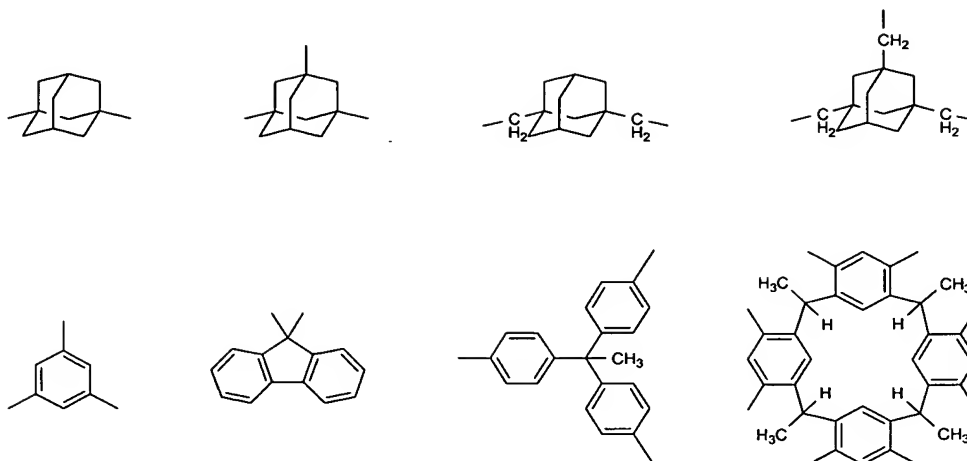


wherein Ar is a phenyl group or a naphthyl group substituted with RO- and/or ROCO-,
wherein R, RO-, and ROCO- are groups reactive with extreme ultraviolet radiation or groups
reactive with an effect of a chromophore active to extreme ultraviolet radiation, and

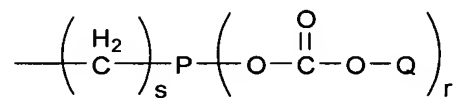
X, Y, and Z individually represent a single bond or an ether bond, and $l + m + n = 2$,
3, 4, or 8.

Claim 25 (New): The photoresist composition according to claim 24, wherein the
extreme ultraviolet-radiation reactive organic compound is in an amorphous state at room
temperature and the average diameter of the molecule is 2 nm or less.

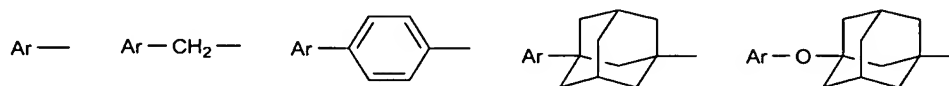
Claim 26 (New): The photoresist composition according to claim 24, wherein A is an
organic group represented by any of the following formulas,



B, C, and D are individually a hydrogen atom, a tert-butyl group, tert-butyloxycarbonylmethyl group, tert-butyloxycarbonyl group, 1-tetrahydropyranyl group, 1-tetrahydrofuranyl group, 1-ethoxyethyl group, 1-phenoxyethyl group, an organic group shown by the formula,

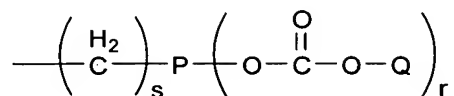


wherein P is an aromatic group having 6 to 20 carbon atoms with a valence of (r + 1), Q represents an organic group having 4 to 30 carbon atoms, r is an integer of 1 to 10, and s is an integer of 0 to 10, or an organic group represented by any of the following formulas,



wherein Ar is a phenyl group or a naphthyl group substituted with RO- and/or ROCO-, wherein R is a hydrogen atom, a tert-butyl group, tert-butyloxycarbonylmethyl group, tert-butyloxycarbonyl group, 1-tetrahydropyranyl group, 1-tetrahydrofuranyl group, 1-

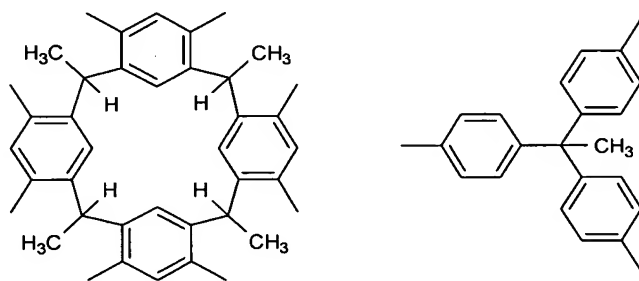
ethoxyethyl group, 1-phenoxyethyl group, or an organic group shown by the following formula,



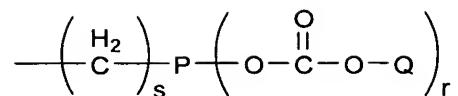
wherein P is an aromatic group having 6 to 20 carbon atoms with a valence of (r + 1), Q represents an organic group having 4 to 30 carbon atoms, r is an integer of 1 to 10, and s is an integer of 0 to 10, and

X, Y, and Z individually represent a single bond or an ether bond.

Claim 27 (New): The photoresist composition according to claim 24, wherein A is any one of the organic groups represented by the following formulas,



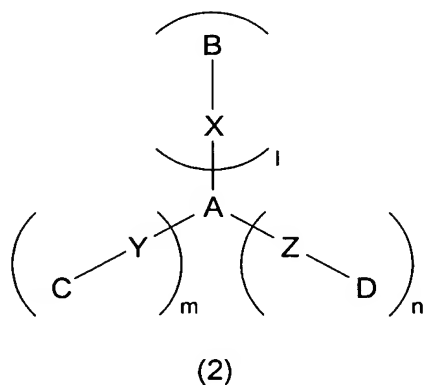
B, C, and D are individually a hydrogen atom, a tert-butyl group, tert-butyloxycarbonylmethyl group, tert-butyloxycarbonyl group, 1-tetrahydropyranyl group, 1-tetrahydrofuranyl group, 1-ethoxyethyl group, 1-phenoxyethyl group, or an organic group shown by the following formula,



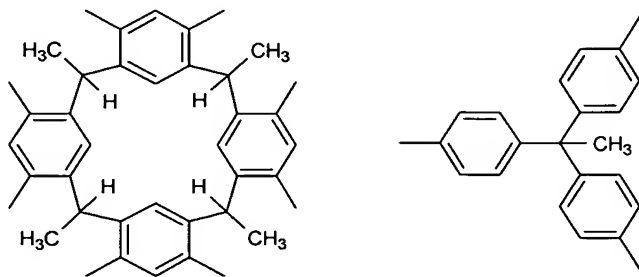
wherein P is an aromatic group having 6 to 20 carbon atoms with a valence of (r + 1), Q represents an organic group having 4 to 30 carbon atoms, r is an integer of 1 to 10, and s is an integer of 0 to 10, and

X, Y, and Z are ether bonds.

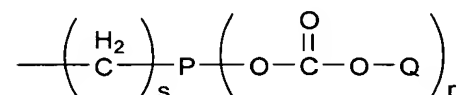
Claim 28 (New): A photoresist composition comprising a photoresist base material that is a radiation-reactive organic compound shown by formula (2), obtained by washing with an acidic aqueous solution and processing with an ion-exchange resin, a photoacid generator or a photobase generator, and a quenching agent,



wherein A is an organic group represented by one of the following formulas,



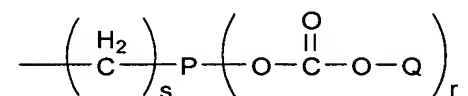
B, C, and D are individually a tert-butyloxycarbonylmethyl group, tert-butyloxycarbonyl group, or an organic group shown by formula,



wherein P is an aromatic group having 6 to 20 carbon atoms with a valence of (r + 1), Q represents an organic group having 4 to 30 carbon atoms, r is an integer of 1 to 10, and s is an integer of 0 to 10, and

X, Y, and Z individually represent a single bond or an ether bond, and 1 + m + n = 3 or 8.

Claim 29 (New): The photoresist composition according to claim 28, wherein the organic group shown by the following formula,



is a 4-(tert-butoxycarbonyloxy)benzyl group or a 3,5-di(tert-butoxycarbonyloxy)benzyl group.

Claim 30 (New): The photoresist composition according to claim 28, wherein the radiation is extreme ultraviolet radiation or an electron beam.

Claim 31 (New): The photoresist composition according to claim 24, wherein at least one of B, C, and D is a hydrogen atom and X, Y, and Z are ether bonds.

Claim 32 (New): The photoresist composition according to claim 24, wherein the basic impurity content of the photoresist base material is not more than 10 ppm.

Claim 33 (New): A method for microfabrication by lithography using the photoresist composition according to claim 21.

Claim 34 (New): A semiconductor device prepared using the photoresist composition according to claim 21.